NEW PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

TACHIBANA, et al.

Atty. Dck. No.: 100353-00185

Serial No.: Unknown

Examiner: Unknown

Filed: March 25, 2004

Art Unit: Unknown

For: SEMICONDUCTOR INTEGRATED CIRCUIT

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Date: March 25, 2004

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the information items listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each item is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the items be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

merits	This Information Disclosure Statement is being filed (a) within three months U.S. filing date, OR (b) before the mailing date of a first Office Action on the in the present application, OR (c) accompanies a Request for Continued ination. No certification or fee is required.
	This Information Disclosure Statement is being filed more than three months he U.S. filing date AND after the mailing date of the first Office Action on the but before the mailing date of a Final Rejection or Notice of Allowance.
	a. I hereby certify that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(1).
	b. I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(2).

		CFR §1.17(p). Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300 as needed to ensure consideration of the disclosed information.				
	Allowathe Infamour	This Information Disclosure Statement is being filed more than three months the U.S. filing date and after the mailing date of a Final Rejection or Notice of ance, but before payment of the Issue Fee. Applicant(s) hereby petition(s) that formation Disclosure Statement be considered. Attached is our check in the nt of \$180.00 in payment of the petition fee under 37 CFR §1.17(i)(1). Please e any fee deficiency or credit any overpayment to Deposit Account No. 01-2300 eded to ensure consideration of the disclosed information.				
		a. I hereby certify that each item of information contained in this Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(1).				
		b. I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 CFR §1.97(e)(2).				
\boxtimes	4. attach	English-language Abstracts of the non-English language references are ed hereto.				
		Respectfully submitted				

Charles M. Marmelstein Registration No. 25,895

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO. SERIAL NO. 100353-00185 Unknown APPLICANT TACHIBANA, et al.

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

FILING DATE GROUP March 25, 2004 Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
	AA						
	AB						
	AC						
	AD						
	AE						

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRA YES	NSLAT	ION PART.
AF	05-204479	August 13, 1993	Japan					х
 AG	06-309052	November 4, 1994	Japan					х
АН	08-186484	July 16, 1996	Japan					х
 AI	10-198447	July 31, 1998	Japan					х
AJ	2001-147725	May 29, 2001	Japan					х
 AK	2002-99336	April 5, 2002	Japan					х
AL	2003-78366	March 14, 2003	Japan					х

OTHER REFERENCES (Including Author Title Date Pertinent Pages Etc.)

АМ	G. Tzanateas, C.A.T. Salama, and Y.P. Tsividis, "A CMOS Bandgap Voltage Reference," IEEE Journal of Solid-State Circuits, Vol. SC-14, No. 3, pp. 655-657, June 1979
AN	K.N. Leung, and P. K. T. Mok, "A Sub-1-V 15-ppm/°C CMOS Bandgap Voltage Reference Without Requiring Low Threshold Voltage Devices," IEEE Journal of Solid-State Circuits, Vol. 37, No. 4, pp. 526-530, April 2002
AO	A. Boni, "Op-Amps and Startup Circuits for CMOS Bandgap References With Near 1-V Supply," IEEE Journal of Solid-State Circuits, Vol. 37, No. 10, pp. 1339-1343, October 2002
AP	H. Banba, H. Shiga, A. Umezawa, T. Miyaba, T. Tanzawa, S. Atsumi, and K. Sakui, "A CMOS Bandgap Reference Circuit with Sub-1-V Operation," IEEE Journal of Solid-State Circuits, Vol. 34, No. 5, pp. 670-674, May 1999

EXAMINER		DATE CONSIDERED			
*EXAMINER:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				